

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

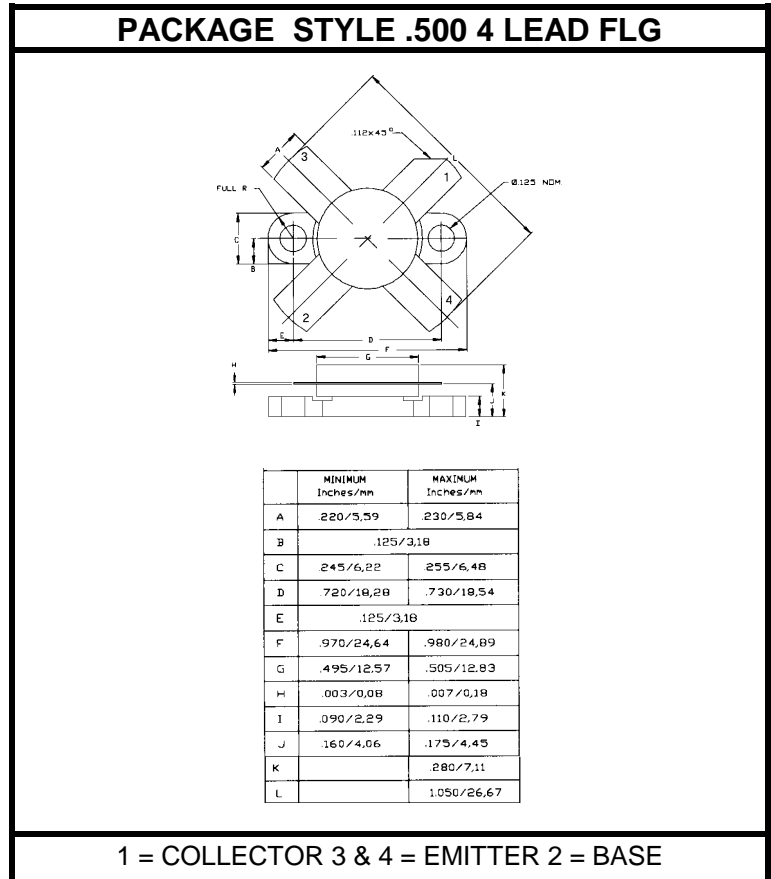
The **ASI SD1019-5** is Designed for VHF Communications up to 136 MHz

FEATURES:

- $P_G = 4.5$ dB Minimum at 150 MHz
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CB}	65 V
V_{CE}	35 V
P_{DISS}	117 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	1.7°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V		1.5		mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0			---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			150	pF
P_{OUT}	$V_{CC} = 13.5$ V $P_{IN} = 10.6$ W $f = 150$ MHz	30			W
P_G		4.5			dB